

## High power PNP epitaxial planar bipolar transistor

#### **Features**

- High breakdown voltage V<sub>CEO</sub> = -250 V
- Complementary to 2STC5949
- Typical f<sub>t</sub> = 25 MHz
- Fully characterized at 125 °C

### **Application**

Audio power amplifier

### **Description**

The device is a PNP transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

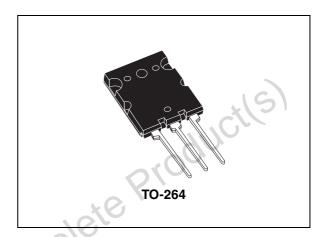


Figure 1. Internal schematic diagram

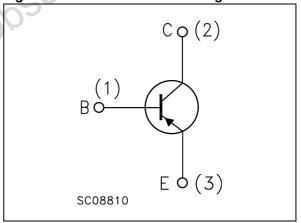


Table 1. Device summary

Order code	Marking	Package	Packaging
2STA2121	2STA2121	TO-264	Tube

Electrical ratings 2STA2121

# 1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-base voltage (I <sub>E</sub> = 0)	-250	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	-250	٧
V <sub>EBO</sub>	Emitter-base voltage (I <sub>C</sub> = 0)	-6	٧
I <sub>C</sub>	Collector current	-17	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5ms)	-34	Α
P <sub>TOT</sub>	Total dissipation at T <sub>c</sub> = 25 °C	220	W
T <sub>stg</sub>	Storage temperature	-65 to 150	o.c
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

Sym	bol	Parameter		Value	Unit
R <sub>thj-c</sub>	ase Th	ermal resistance junction-case	max	0.568	°C/W
		· · · · · · · · · · · · · · · · · · ·	76,		
		, c	0,		
		Ob.			
		16)			
		11/0			
	- 40	Juci(s)			
	210				
× (2)					
Obsolete					
60					
002					

2/8

## 2 Electrical characteristics

(T<sub>case</sub> = 25 °C; unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> = 0)	V <sub>CB</sub> = -250 V			-5	μΑ
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = -6 V			-5	μΑ
V <sub>(BR)CEO</sub> <sup>(1)</sup>	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = -50 mA	-250		46	V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = -100 μA	-250	101		V
V <sub>(BR)EBO</sub> <sup>(1)</sup>	Emitter-base breakdown voltage ( $I_C = 0$ )	I <sub>E</sub> = -1 mA	-6	)		V
V <sub>CE(sat)</sub> (1)	Collector-emitter saturation voltage	$I_C = -8 \text{ A}$ $I_B = -800 \text{ mA}$			-3	V
V <sub>BE</sub> <sup>(1)</sup>	Base-emitter voltage	$I_{C} = -7 \text{ A}$ $V_{CE} = -5 \text{ V}$			-1.5	V
h <sub>FE</sub>	DC current gain	$I_C = -1 \text{ A}$ $V_{CE} = -5 \text{ V}$ $I_C = -7 \text{ A}$ $V_{CE} = -5 \text{ V}$	80 35		160	
f <sub>T</sub>	Transition frequency	$I_C = -1 A$ $V_{CE} = -5 V$		25		MHz

<sup>1.</sup> Pulsed duration = 300 μs, duty cycle ≤ 1.5%

5/

Electrical characteristics 2STA2121

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve

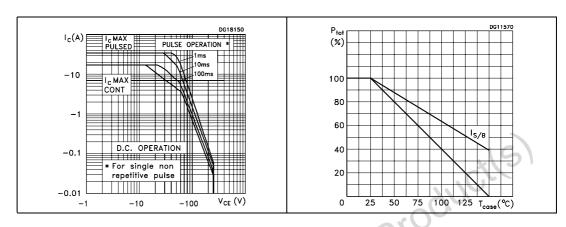


Figure 4. Output characteristics

Figure 5. DC current gain

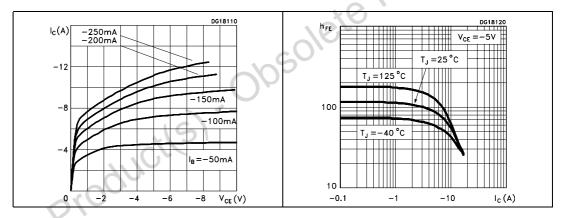
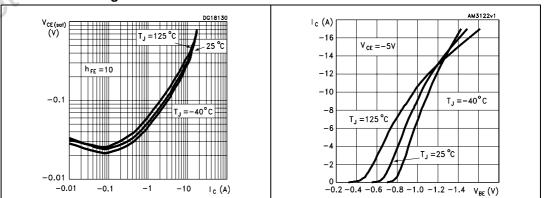


Figure 6. Collector-emitter saturation voltage

Figure 7. Base-emitter voltage



4/8

## 3 Package mechanical data

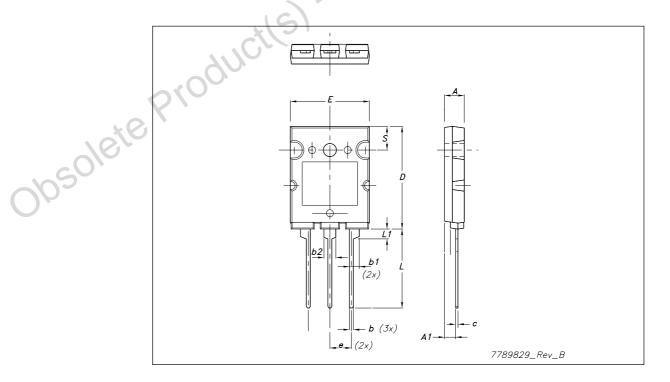
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Produci(s). Obsolete Produci(s)

577

#### **TO-264 Mechanical data**

Dim.	mm.				
	Min.	Тур	Max.		
Α	4.80		5.20		
A1	2.50		3.10		
b	0.90	1.0	1.25		
b1		2.5	(C)		
b2		2.8	40,		
С	0.50	0.60	0.85		
D	25.6		26.4		
Е	19.80	20,	20.20		
е	5.15	10,1	5.75		
L	19.50	c0/2	20.50		
L1	2.30	75	2.70		
øΡ	3.55	9	3.65		



2STA2121 Revision history

## 4 Revision history

Table 5. Document revision history

Date	Revision	Changes
23-Nov-2007	1	Initial release
08-May-2008	2	Added new graphics.
12-Nov-2008	3	Document status promoted from preliminary data to datasheet

Obsolete Product(s).

#### Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZE REPRESENTATIVE OF ST, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS, WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2008 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

577

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by STMicroelectronics manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G

NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2330 NTE2353 NTE316 NTE65 C4460 SBC846BLT3G 2SA1419T
TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176

FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E

CMXT2207 TR CPH6501-TL-E MCH4021-TL-E TTC012(Q) BULD128DT4 DDTC114EUAQ-7-F NJL0281DG NSS20500UW3TBG

732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H SZT1010T1G 873787E